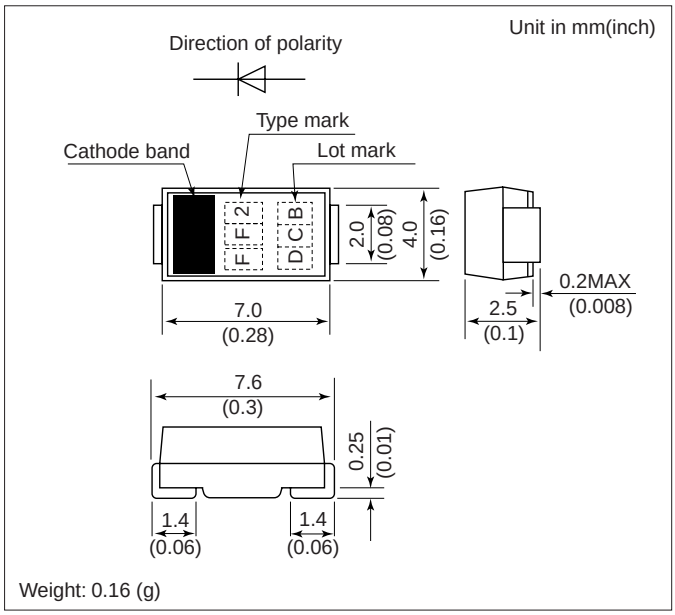
# DFM3MF

## FEATURES

- For high speed switching
- Soft recovery, low noise.
- Low loss, high efficiency.

## OUTLINE DRAWING




Weight: 0.16 (g)

## ABSOLUTE MAXIMUM RATINGS

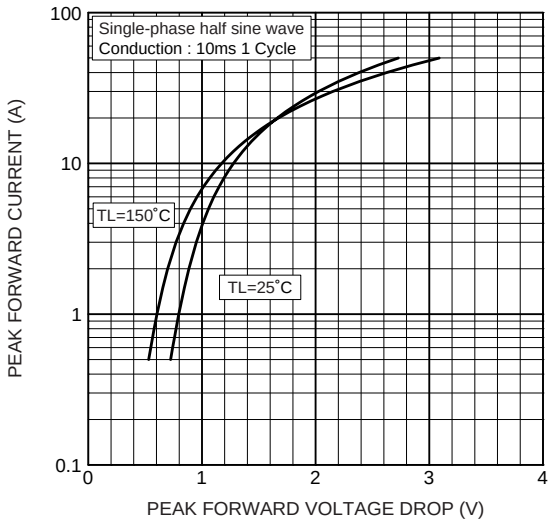
| Item | Type | | DFM3MF2 |
|---|---|---|---|
| Repetitive Peak Reverse Voltage | $V_{RRM}$ | V | 200 |
| Average Forward Current | $I_{F(AV)}$ | A | 3.0 (Single-phase half sine wave 180° conduction, TL = 98°C) |
| Surge(Non-Repetitive) Forward Current | $I_{FSM}$ | A | 50 ( Without PIV, 10ms conduction, Tj = 40°C start ) |
| Operating Junction Temperature | $T_j$ | °C | -40 ~ +150 |
| Storage Temperature | $T_{stg}$ | °C | -40 ~ +150 |

## CHARACTERISTICS($T_L$=25°C)

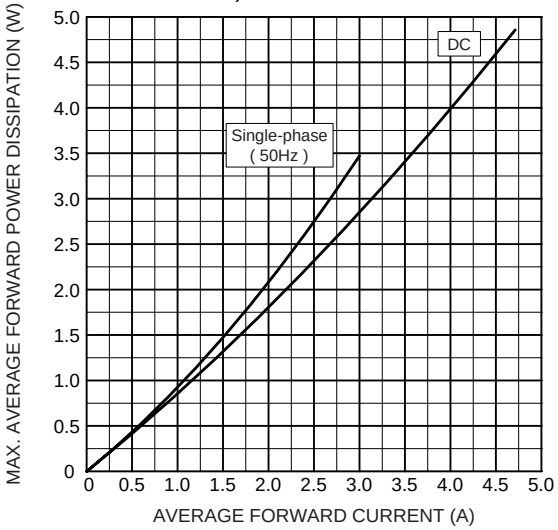
| Item | Symbols | Units | Min. | Typ. | Max. | Test Conditions |
|---|---|---|---|---|---|---|
| Peak Reverse Current | $I_{RRM}$ | μA | — | — | 10 | $V_R = V_{RRM}$ |
| Peak Forward Voltage | $V_{FM}$ | V | — | — | 0.95 | $I_{FM}$=3.0Ap, Single-phase half sine wave 1 cycle |
| Reverse Recovery Time | Trr | ns | — | — | 35 | $I_F$=0.5A, $I_{rp}$=1.0A, 25%recovery |
| Steady State Thermal Impedance | $R_{th(j-a)}$ | °C/W | — | — | 90 | On glass-epoxi substrate ( ☐ 50mm) |
| | $R_{th(j-l)}$ | | | | 15 | Soldering land( ☐ 10mm) |

# DFM3MF

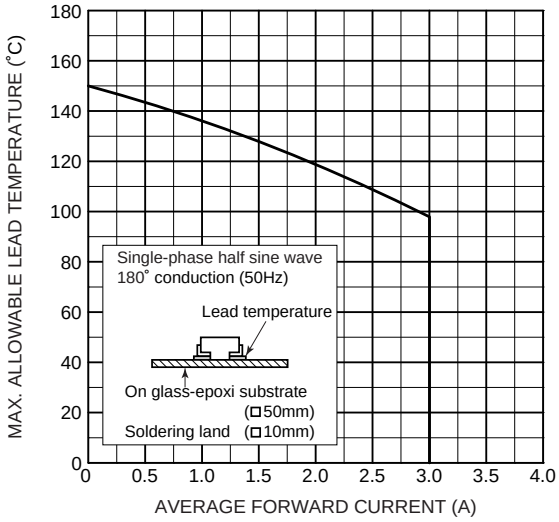
Forward characteristics



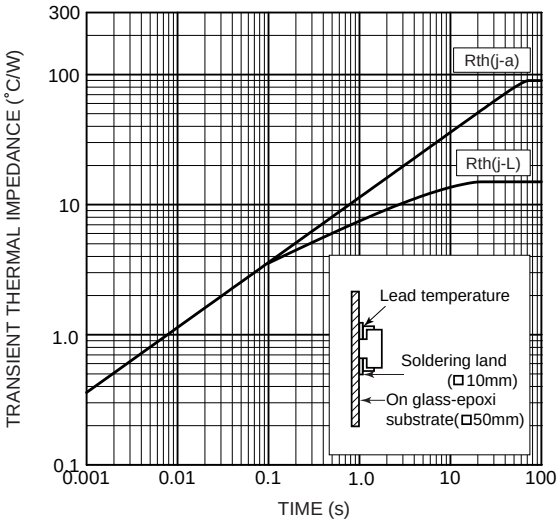

Max. average forward power dissipation
(Resistive or inductive load)



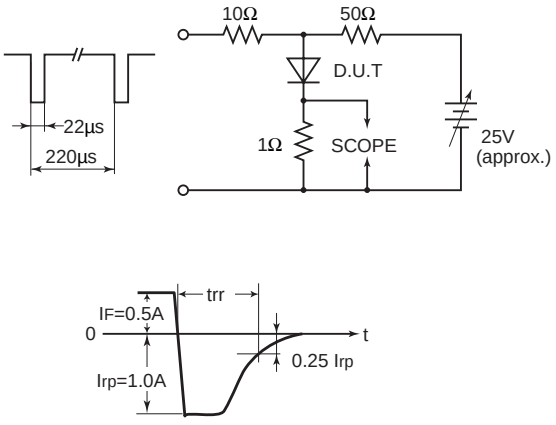

Max. allowable lead temperature
(Resistive or inductive load)




Transient thermal impedance




Reverse recovery time(trr) test circuit



# HITACHI POWER SEMICONDUCTORS

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